P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY							
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)				
- 30	1.9 at V _{GS} = - 10 V	- 130	150 °C				
- 30	2.7 at V _{GS} = - 4.5 V	- 130	150 nC				

FEATURES

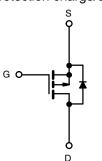
- DT-Trench Power MOSFET
- 100 % Rg and UIS Tested
- · RoHS and Halogen-Free Compliant



APPLICATIONS

- Notebook AC-in load switch
- · Battery protection charge/discharge





P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	- 30	V			
Gate-Source Voltage	V_{GS}	± 20				
Continuous Drain Current (T, I = 150 °C) ^a	T _C = 25 °C	- I _D	- 130			
Continuous Diairi Current (1) = 130 C)	T _C = 100 °C		- 85	Α		
Pulsed Drain Current ^b		I _{DM}	- 390			
Single Pulse Avalanche Energy		E _{AS}	300	mJ		
Maximum Power Dissipation ^c	T _C = 25 °C	P _D	168	W		
Maximum Fower Dissipation	T _C = 100 °C	_ rp	67.5			
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C			

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	UNIT	
Junction-to-Ambient	PCB mount ^d	R _{thJA}	50	°C/W	
Junction-to-Case		R _{thJC}	0.74	0/ • •	

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. $\,$ Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•			•			
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 30			V	
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 1		- 3	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Oata Walla an David Oamani	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V	-		- 1	μΑ	
Zero Gate Voltage Drain Current		V _{DS} = - 24 V, V _{GS} = 0 V, T _J = 55 °C		- 10			
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 130			Α	
	D	V _{GS} = - 10 V, I _D = - 20 A		1.9	2.5		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 20 A		2.7	3.6	mΩ	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = -20 A		100		S	
Dynamic ^b							
Input Capacitance	C _{iss}			12000		pF	
Output Capacitance	C _{oss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		1340			
Reverse Transfer Capacitance	C _{rss}			1640			
Total Gate Charge	Q_g			150		nC	
Gate-Source Charge	Q_{gs}	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 20 A		40			
Gate-Drain Charge	Q_{gd}]		45			
Gate Resistance	R_g	f = 1 MHz		1.9		Ω	
Turn-On Delay Time	t _{d(on)}			35			
Rise Time	t _r	V _{DD} = - 15 V, I _D = - 20 A,		60		ns	
Turn-Off Delay Time	t _{d(off)}	VGEN = - 10 V, Rg = 2.5Ω		180			
Fall Time	t _f			60			
Drain-Source Body Diode Characteristics	3						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 130	Α	
Pulse Diode Forward Current ^a	I _{SM}				- 390		
Body Diode Voltage	V _{SD}	I _S = - 1 A			- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 20 A, di/dt = 100 A/μs, T _{.I} = 25 °C		25		ns	
Body Diode Reverse Recovery Charge	Q _{rr}	Q_{rr} $I_F = -20 \text{ A}, \text{ ul/ul} = 100 \text{ A/}\mu\text{S}, I_J = 25 \text{ C}$		69		nC	

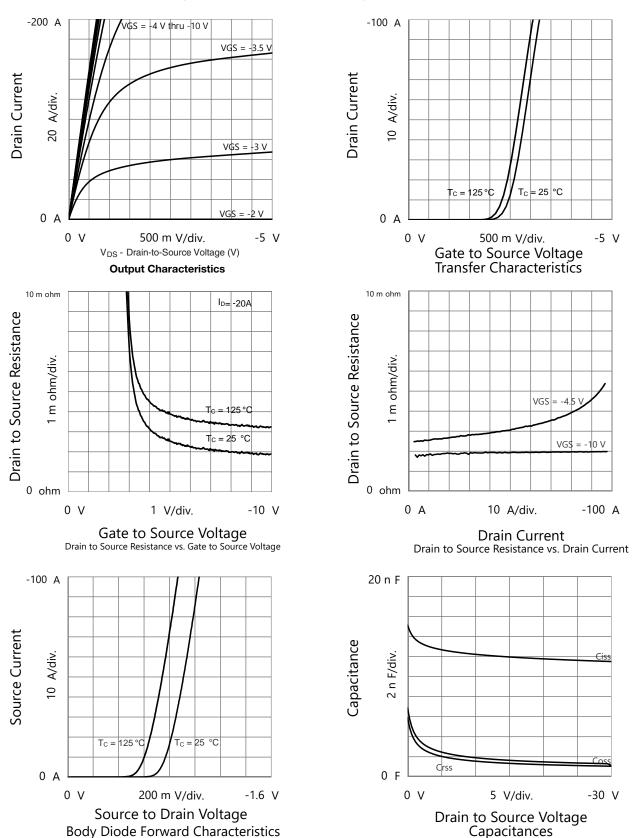
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

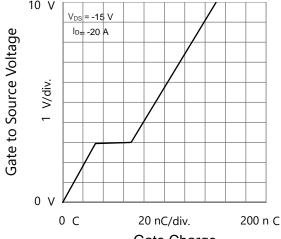
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

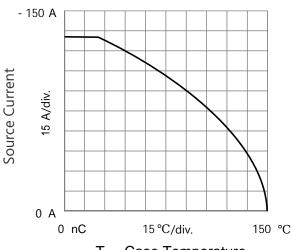




TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

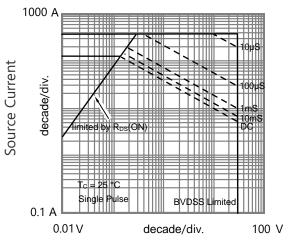


Gate Charge
Gate to Source Voltage vs. GateCharge

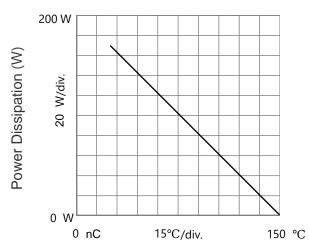


T_C - Case Temperature

Current Derating

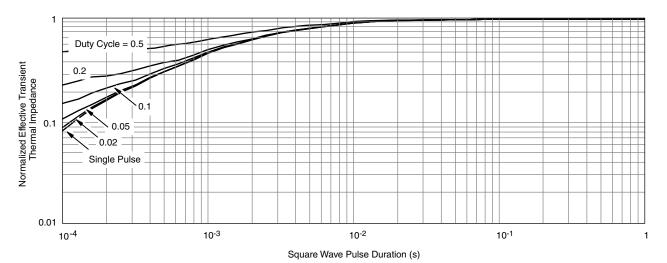


Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature

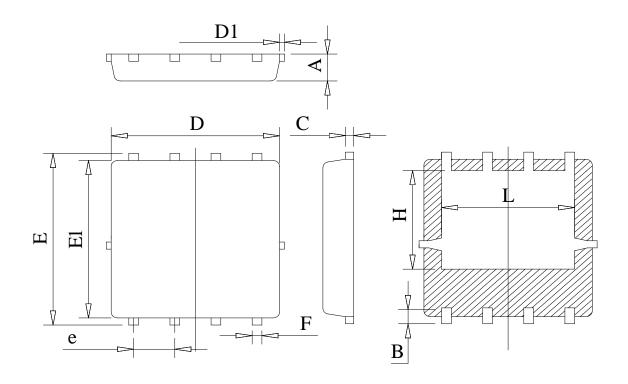
Current Derating



Normalized Thermal Transient Impedance, Junction-to-Case



DFN5X6-8L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Unit: mm

Symbol	Min	Тур	Max
A	0.78	0.95	1.12
В	0.45	0.58	0.78
С	0.18	0.254	0.36
D	4.70	5.20	5.45
D1			0.18
Е	5.85	6.05	6.25
E1	5.38	5.55	5.98
e	1.15	1.27	1.40
F	0.18	0.30	0.52
Н	3.25	3.47	3.70
L	3.75	4.00	4.25

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